

100V NPN HIGH VOLTAGE TRANSISTOR IN TO252 (DPAK)

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

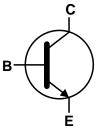
- BV_{CEO} > 100V
- I_C = 3A high Continuous Collector Current
- I_{CM} = 5A Peak Pulse Current
- Ideal for Power Switching or Amplification Applications
- Complementary PNP Type: MJD32CUQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

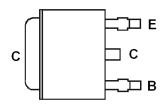
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 [®]
- Weight: 0.34 grams (Approximate)







Device Schematic



Pin Out Configuration Top View

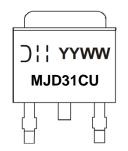
Ordering Information (Notes 4 & 5)

Part nu	mber	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MJD31C	UQ-13	Automotive	MJD31CU	13	16	2,500

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



MJD31CU = Product Type Marking Code

OH = Manufacturers' Code Marking

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 17 = 2017)

WW = Week Code (01 to 53)



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	120	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	3	A
Peak Pulse Collector Current	I _{CM}	5	A
Continuous Base Current	I _B	1	A
Power Dissipation	P _D	15	W

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 6)	3.9			
Power Dissipation	(Note 7)	P_{D}	2.1	W	
	(Note 8)		1.6		
	(Note 6)		32		
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ hetaJA}$	59	2000	
	(Note 8)		80	°C/W	
Thermal Resistance, Junction to Leads	(Note 9)	$R_{ heta JL}$	3.6		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

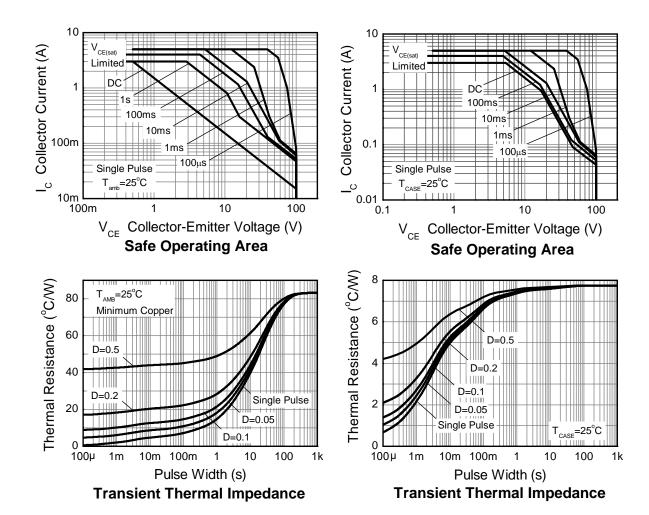
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as note (6), except mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
- Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





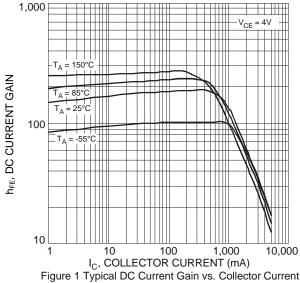
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

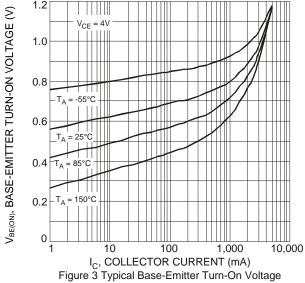
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	120	1	-	V	$I_C = 20\mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	100	-	-	V	$I_C = 30mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	ı	-	V	$I_E = 100\mu A$
Collector-Base Cut-off Current	I _{CBO}	-	1	1	μΑ	V _{CB} = 100V
Collector Cut-off Current	I _{CEO}	=	ı	1	μA	V _{CE} = 60V
Collector Cut-off Current	I _{CES}	-	1	1	μΑ	V _{CE} = 100V
Emitter Cut-off Current	I _{EBO}	-	1	1	μΑ	$V_{EB} = 5V$
	V _{CE(sat)}	-	_	300	mV	$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Voltage (Note 11)		_	-	500	mV	$I_C = 2A$, $I_B = 200mA$
		=	ı	700	mV	$I_C = 3A$, $I_B = 375mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	_	1.2	V	$I_C = 2A$, $I_B = 200mA$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	=	-	950	mV	$I_C = 1A$, $V_{CE} = 2V$
base-Emilier Fum-On Vollage (Note 11)		-	_	1.4	V	$I_C = 3A$, $V_{CE} = 4V$
DC Current Gain (Note 11)	h _{FE}	25		-	_	$V_{CE} = 4V, I_C = 1A$
DC Current Gain (Note 11)		10	_	50	_	$V_{CE} = 4V$, $I_C = 3A$
Current Signal Current Gain	H _{fe}	20	ı	-	-	$V_{CE} = 10V$, $I_{C} = 0.5A$, $f = 1kHz$
Current Gain-Bandwidth Product	f⊤	3.0	-	_	MHz	$I_C = 0.5A$, $V_{CE} = 10V$, $f = 1MHz$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

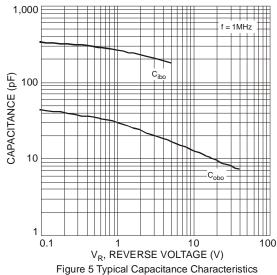


Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





vs. Collector Current



 $I_C/I_B = 8$ V_{CE(SAT)}, COLLECTOR-EMITTER SATURATION VOLTAGE (V) 0.1 0.01 10 100 1,000 I_C, COLLECTOR CURRENT (mA) 10,000

Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

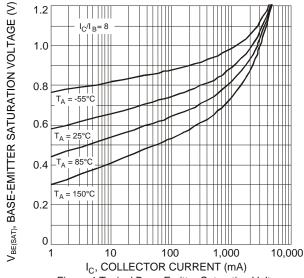


Figure 4 Typical Base-Emitter Saturation Voltage vs. Collector Current

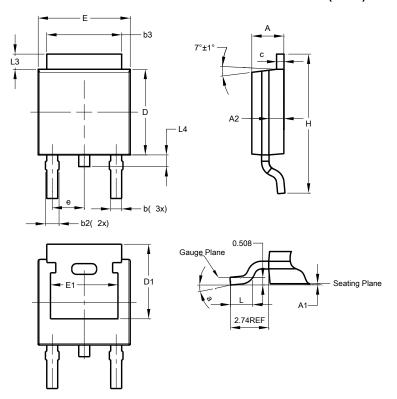
MJD31CUQ



Package Outline Dimensions

 $\label{lem:please} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

TO252 (DPAK)

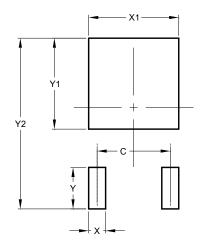


TO252 (DPAK)				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
A 1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
b	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
С	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	-	-	
е	-	-	2.286	
Е	6.45	6.70	6.58	
E1	4.32	-	1	
Н	9.40	10.41	9.91	
٦	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°	-	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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